Amendments to the Claims:

This listing of claims replaces all prior versions and listings of claims in the application:

Listing of Claims:

1-5. (Canceled)

6. (Currently Amended) A method of manufacturing a light emitting device, said method comprising:

forming at least a transparent protrusion;

forming a pixel electrode to overlap the transparent protrusion;

forming a light emitting layer to overlap the pixel electrode; and

forming ~~a cathode~~ an electrode over the light emitting layer.

7. (Currently Amended) A personal computer comprising a main body, a casing, a display portion, and a keyboard, said personal computer using a light emitting device:

wherein said light emitting device comprises:

at least a transparent protrusion;

a pixel electrode over the transparent protrusion;

a light emitting layer over the pixel electrode; and

~~a cathode~~ an electrode over the light emitting layer,

wherein a surface of the ~~cathode~~ electrode in contact with the light emitting layer is uneven.

8. (Original) A personal computer according to claim 7, further comprising:

an insulating film in transverse direction of the transparent protrusion,

wherein the insulating film has a high light absorption property.

9. (Original) A personal computer according to claim 7,

wherein the transparent protrusion is a microlens.

10. (Currently Amended) A portable telephone comprising a main body, a sound output portion, a sound input portion, a display portion, operation switches, and an antenna, said portable telephone using a light emitting device:

wherein said light emitting device comprises:

at least a transparent protrusion;

a pixel electrode over the transparent protrusion;

a light emitting layer over the pixel electrode; and

~~a cathode~~ an electrode over the light emitting layer,

wherein a surface of the ~~cathode~~ electrode in contact with the light emitting layer is uneven.

11. (Original) A portable telephone according to claim 10, further comprising:

an insulating film in a transverse direction of the transparent protrusion,

wherein the insulating film has a high light absorption property.

12. (Original) A portable telephone according to claim 10,

wherein the transparent protrusion is a microlens.

13. (Original) A portable telephone according to claim 10, further comprising an operation panel, a connecting portion, and a power source switch.

14. (Previously Presented) A method according to claim 6, further comprising:

forming an insulating film in a transverse direction of the transparent protrusion, wherein the insulating film has a high light absorption property.

15. (Previously Presented) A method according to claim 6, further comprising:

forming a thin film transistor on a substrate, wherein the thin film transistor comprises a semiconductor film and a gate electrode;

forming an insulating film over the thin film transistor;

forming a first opening in the insulating film;

forming a wiring over the insulating film, wherein the wiring is electrically connected to the semiconductor film through the first opening; and

forming at least one second opening in the insulating film.

16. (Previously Presented) A method according to claim 6, further comprising:

forming a thin film transistor on a substrate, wherein the thin film transistor comprises a semiconductor film and a gate electrode;

forming an insulating film over the thin film transistor, wherein the insulating film has a high light absorption property;

forming a first opening in the insulating film;

forming a wiring over the insulating film, wherein the wiring is electrically connected to the semiconductor film through the first opening; and

forming at least one second opening in the insulating film.

17. (Previously Presented) A method according to claim 6, further comprising:

forming a thin film transistor on a substrate, wherein the thin film transistor comprises a semiconductor film and a gate electrode;

forming a first insulating film over the thin film transistor;

forming a first opening in the first insulating film;

forming a wiring over the first insulating film, wherein the wiring is electrically connected to the semiconductor film through the first opening;

forming a second insulating film in contact with the first insulating film; and

forming a second opening in the second insulating film.

18. (Previously Presented) A method according to claim 6, further comprising:

forming a thin film transistor on a substrate, wherein the thin film transistor comprises a semiconductor film and a gate electrode;

forming a first insulating film over the thin film transistor;

forming a first opening in the first insulating film;

forming a wiring over the first insulating film, wherein the wiring is electrically connected to the semiconductor film through the first opening;

forming a second insulating film in contact with the first insulating film, wherein the second insulating film has a high light absorption property; and

forming a second opening in the second insulating film.

19. (Previously Presented) A method according to claim 6, wherein the transparent protrusion comprises a microlens.

20. (Previously Presented) A method according to claim 6, wherein the light emitting layer comprises at least one of an organic material and an inorganic material.

21. (Currently Amended) A method according to claim 6, wherein a surface of the ~~cathode~~ electrode in contact with the light emitting layer is uneven.

22. (Previously Presented) A personal computer according to claim 7, wherein the light emitting layer comprises at least one of an organic material and an inorganic material.

23. (Previously Presented) A portable telephone according to claim 10, wherein the light emitting layer comprises at least one of an organic material and an inorganic material.

24. (Currently Amended) A method of manufacturing a light emitting device, said method comprising:

forming at least a protrusion having a property of transmitting light;

forming a pixel electrode to overlap the protrusion;

forming a light emitting layer to overlap the pixel electrode; and

forming ~~a cathode~~ an electrode over the light emitting layer.

25. (Previously Presented) A method according to claim 24, further comprising:

forming an insulating film in a transverse direction of the protrusion, wherein the insulating film has a high light absorption property.

26. (Previously Presented) A method according to claim 24, further comprising:

forming a thin film transistor on a substrate, wherein the thin film transistor comprises a semiconductor film and a gate electrode;

forming an insulating film over the thin film transistor;

forming a first opening in the insulating film;

forming a wiring over the insulating film, wherein the wiring is electrically connected to the semiconductor film through the first opening; and

forming at least one second opening in the insulating film.

27. (Previously Presented) A method according to claim 24, further comprising:

forming a thin film transistor on a substrate, wherein the thin film transistor comprises a semiconductor film and a gate electrode;

forming an insulating film over the thin film transistor, wherein the insulating film has a high light absorption property;

forming a first opening in the insulating film;

forming a wiring over the insulating film, wherein the wiring is electrically connected to the semiconductor film through the first opening; and

forming at least one second opening in the insulating film.

28. (Previously Presented) A method according to claim 24, further comprising:

forming a thin film transistor on a substrate, wherein the thin film transistor comprises a semiconductor film and a gate electrode;

forming a first insulating film over the thin film transistor;

forming a first opening in the first insulating film;

forming a wiring over the first insulating film, wherein the wiring is electrically connected to the semiconductor film through the first opening;

forming a second insulating film in contact with the first insulating film; and

forming a second opening in the second insulating film.

29. (Previously Presented) A method according to claim 24, further comprising:

forming a thin film transistor on a substrate, wherein the thin film transistor comprises a semiconductor film and a gate electrode;

forming a first insulating film over the thin film transistor;

forming a first opening in the first insulating film;

forming a wiring over the first insulating film, wherein the wiring is electrically connected to the semiconductor film through the first opening;

forming a second insulating film in contact with the first insulating film, wherein the second insulating film has a high light absorption property; and

forming a second opening in the second insulating film.

30. (Previously Presented) A method according to claim 24, wherein the light emitting layer comprises at least one of an organic material and an inorganic material.

31. (Currently Amended) A method according to claim 24, wherein a surface of the ~~cathode~~ electrode in contact with the light emitting layer is uneven.

32. (Currently Amended) A method of manufacturing a light emitting device, said method comprising:

forming at least a microlens;

forming a pixel electrode to overlap the microlens;

forming a light emitting layer to overlap the pixel electrode; and

forming ~~a cathode~~ an electrode over the light emitting layer.

33. (Previously Presented) A method according to claim 32, further comprising:

forming an insulating film in a transverse direction of the microlens, wherein the insulating film has a high light absorption property.

34. (Previously Presented) A method according to claim 32, further comprising:

forming a thin film transistor on a substrate, wherein the thin film transistor comprises a semiconductor film and a gate electrode;

forming an insulating film over the thin film transistor;

forming a first opening in the insulating film;

forming a wiring over the insulating film, wherein the wiring is electrically connected to the semiconductor film through the first opening; and

forming at least one second opening in the insulating film.

35. (Previously Presented) A method according to claim 32, further comprising:

forming a thin film transistor on a substrate, wherein the thin film transistor comprises a semiconductor film and a gate electrode;

forming an insulating film over the thin film transistor, wherein the insulating film has a high light absorption property;

forming a first opening in the insulating film;

forming a wiring over the insulating film, wherein the wiring is electrically connected to the semiconductor film through the first opening; and

forming at least one second opening in the insulating film.

36. (Previously Presented) A method according to claim 32, further comprising:

forming a thin film transistor on a substrate, wherein the thin film transistor comprises a semiconductor film and a gate electrode;

forming a first insulating film over the thin film transistor;

forming a first opening in the first insulating film;

forming a wiring over the first insulating film, wherein the wiring is electrically connected to the semiconductor film through the first opening;

forming a second insulating film in contact with the first insulating film; and

forming a second opening in the second insulating film.

37. (Previously Presented) A method according to claim 32, further comprising:

forming a thin film transistor on a substrate, wherein the thin film transistor comprises a semiconductor film and a gate electrode;

forming a first insulating film over the thin film transistor;

forming a first opening in the first insulating film;

forming a wiring over the first insulating film, wherein the wiring is electrically connected to the semiconductor film through the first opening;

forming a second insulating film in contact with the first insulating film, wherein the second insulating film has a high light absorption property; and

forming a second opening in the second insulating film.

38. (Previously Presented) A method according to claim 32, wherein the light emitting layer comprises at least one of an organic material and an inorganic material.

39. (Currently Amended) A method according to claim 32, wherein a surface of the ~~cathode~~ electrode in contact with the light emitting layer is uneven.

40. (Currently Amended) A method of manufacturing a light emitting device, said method comprising:

forming at least a layer containing a transparent material;

forming a pixel electrode to overlap the layer;

forming a light emitting layer to overlap the pixel electrode; and

forming ~~a cathode~~ an electrode over the light emitting layer,

wherein a surface of the ~~cathode~~ electrode in contact with the light emitting layer is uneven.

41. (Previously Presented) A method according to claim 40, further comprising:

forming an insulating film in a transverse direction of the layer, wherein the insulating film has a high light absorption property.

42. (Previously Presented) A method according to claim 40, further comprising:

forming a thin film transistor on a substrate, wherein the thin film transistor comprises a semiconductor film and a gate electrode;

forming an insulating film over the thin film transistor;

forming a first opening in the insulating film;

forming a wiring over the insulating film, wherein the wiring is electrically connected to the semiconductor film through the first opening; and

forming at least one second opening in the insulating film.

43. (Previously Presented) A method according to claim 40, further comprising:

forming a thin film transistor on a substrate, wherein the thin film transistor comprises a semiconductor film and a gate electrode;

forming an insulating film over the thin film transistor, wherein the insulating film has a high light absorption property;

forming a first opening in the insulating film;

forming a wiring over the insulating film, wherein the wiring is electrically connected to the semiconductor film through the first opening; and

forming at least one second opening in the insulating film.

44. (Previously Presented) A method according to claim 40, further comprising:

forming a thin film transistor on a substrate, wherein the thin film transistor comprises a semiconductor film and a gate electrode;

forming a first insulating film over the thin film transistor;

forming a first opening in the first insulating film;

forming a wiring over the first insulating film, wherein the wiring is electrically connected to the semiconductor film through the first opening;

forming a second insulating film in contact with the first insulating film; and

forming a second opening in the second insulating film.

45. (Previously Presented) A method according to claim 40, further comprising:

forming a thin film transistor on a substrate, wherein the thin film transistor comprises a semiconductor film and a gate electrode;

forming a first insulating film over the thin film transistor;

forming a first opening in the first insulating film;

forming a wiring over the first insulating film, wherein the wiring is electrically connected to the semiconductor film through the first opening;

forming a second insulating film in contact with the first insulating film, wherein the second insulating film has a high light absorption property; and

forming a second opening in the second insulating film.

46. (Previously Presented) A method according to claim 40, wherein the light emitting layer comprises at least one of an organic material and an inorganic material.

47. (Previously Presented) A method according to claim 40, wherein the layer has a protrusion.

48. (Currently Amended) A method of manufacturing a light emitting device, said method comprising:

forming at least a layer having a property of transmitting light,

forming a pixel electrode to overlap the layer;

forming a light emitting layer to overlap the pixel electrode; and

forming ~~a cathode~~ an electrode over the light emitting layer,

wherein a surface of the ~~cathode~~ electrode in contact with the light emitting layer is uneven.

49. (Previously Presented) A method according to claim 48, further comprising:

forming an insulating film in a transverse direction of the layer, wherein the insulating film has a high light absorption property.

50. (Previously Presented) A method according to claim 48, further comprising:

forming a thin film transistor on a substrate, wherein the thin film transistor comprises a semiconductor film and a gate electrode;

forming an insulating film over the thin film transistor;

forming a first opening in the insulating film;

forming a wiring over the insulating film, wherein the wiring is electrically connected to the semiconductor film through the first opening; and

forming at least one second opening in the insulating film.

51. (Previously Presented) A method according to claim 48, further comprising:

forming a thin film transistor on a substrate, wherein the thin film transistor comprises a semiconductor film and a gate electrode;

forming an insulating film over the thin film transistor, wherein the insulating film has a high light absorption property;

forming a first opening in the insulating film;

forming a wiring over the insulating film, wherein the wiring is electrically connected to the semiconductor film through the first opening; and

forming at least one second opening in the insulating film.

52. (Previously Presented) A method according to claim 48, further comprising:

forming a thin film transistor on a substrate, wherein the thin film transistor comprises a semiconductor film and a gate electrode;

forming a first insulating film over the thin film transistor;

forming a first opening in the first insulating film;

forming a wiring over the first insulating film, wherein the wiring is electrically connected to the semiconductor film through the first opening;

forming a second insulating film in contact with the first insulating film; and

forming a second opening in the second insulating film.

53. (Previously Presented) A method according to claim 48, further comprising:

forming a thin film transistor on a substrate, wherein the thin film transistor comprises a semiconductor film and a gate electrode;

forming a first insulating film over the thin film transistor;

forming a first opening in the first insulating film;

forming a wiring over the first insulating film, wherein the wiring is electrically connected to the semiconductor film through the first opening;

forming a second insulating film in contact with the first insulating film, wherein the second insulating film has a high light absorption property; and

forming a second opening in the second insulating film.

54. (Previously Presented) A method according to claim 48, wherein the light emitting layer comprises at least one of an organic material and an inorganic material.

55. (Previously Presented) A method according to claim 48, wherein the layer has a protrusion.

56. (Previously Presented) A method according to claim 48, wherein the layer contains a transparent material.

57. (New) A method according to claim 6, wherein the electrode is a cathode.

58. (New) A personal computer according to claim 7, wherein the electrode is a cathode.

59. (New) A portable telephone according to claim 10, wherein the electrode is a cathode.

60. (New) A method according to claim 24, wherein the electrode is a cathode.

61. (New) A method according to claim 32, wherein the electrode is a cathode.

62. (New) A method according to claim 40, wherein the electrode is a cathode.

63. (New) A method according to claim 48, wherein the electrode is a cathode.